



MJD31CQ

100V NPN HIGH VOLTAGE TRANSISTOR IN TO252

Description

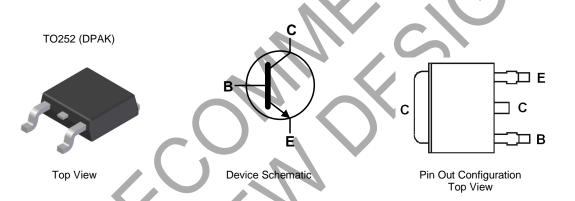
This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of Automotive Applications.

Features

- BV_{CEO} > 100V
- I_C = 3A high Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary PNP Type: MJD32CQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.34 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD31CQ-13	Automotive	MJD31C	13	16	2,500

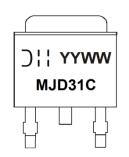
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- and Lead-free.

 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.

 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MJD31C = Product Type Marking Code Oll = Manufacturers' code marking YYWW = Date Code Marking YY = Last Digit of Year (ex: 16 = 2016) WW = Week Code (01 - 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	3	А
Peak Pulse Collector Current	I _{CM}	5	А
Continuous Base Current	I _B	1	A
Power Dissipation	P_{D}	15	W

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		3.9	
Power Dissipation	(Note 7)	P _D	2.1	W
	(Note 8)		1.6	
	(Note 6)		32	Ť
Thermal Resistance, Junction to Ambient Air	(Note 7)	R _{BJA}	59	°C/W
	(Note 8)		80	C/VV
Thermal Resistance, Junction to Leads	(Note 9)	$R_{ heta JL}$	8.4	
Operating and Storage Temperature Range		$T_{ m J}, T_{ m STG}$	-55 to +150	°C

ESD Ratings (Note 10)

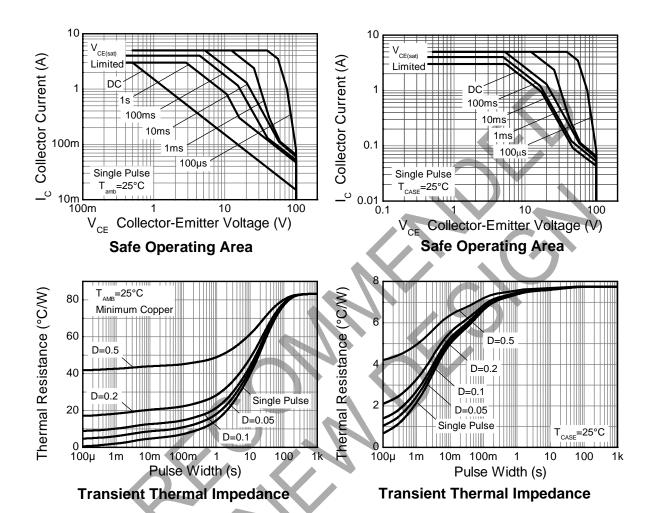
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm × 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

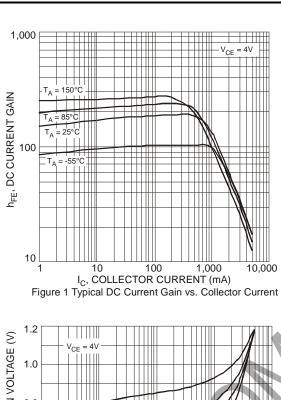
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	100	_	_	V	$I_C = 30 \text{mA}, I_B = 0$
Collector Cut-off Current	ICEO		_	1	μΑ	$V_{CB} = 60V, I_B = 0$
Collector Cut-off Current	ICES	_	_	1	μΑ	V _{CE} = 100V, V _{EB} = 0
Emitter Cut-off Current	I _{EBO}	_	_	1	μΑ	$V_{EB} = 5V, I_{C} = 0$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	_	1.2	V	$I_C = 3.0A$, $I_B = 375mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	1.8	V	$I_C = 3A, V_{CE} = 4V$
DC Current Gain (Note 11)	h	25		_		$V_{CE} = 4V$, $I_C = 1A$
DC Current Gain (Note 11)	h _{FE}	10		50		$V_{CE} = 4V$, $I_C = 3A$
Current Signal Current Gain	H _{fe}	20	_		/	$V_{CE} = 10V, I_{C} = 0.5A, f = 1KHz$
Current Gain-Bandwidth Product	f _T	3.0		_	MHz	$I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}, f = 1 \text{MHz}$

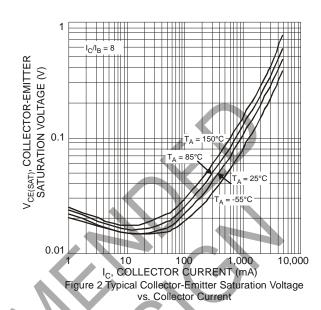
Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

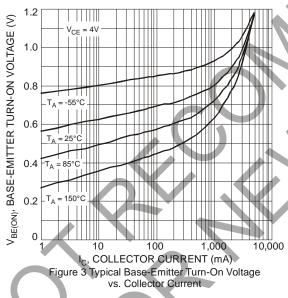


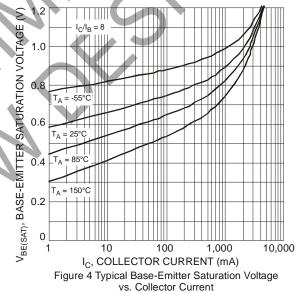


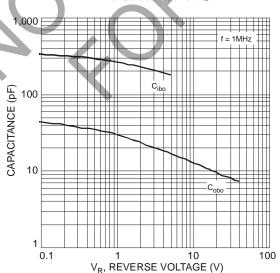
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









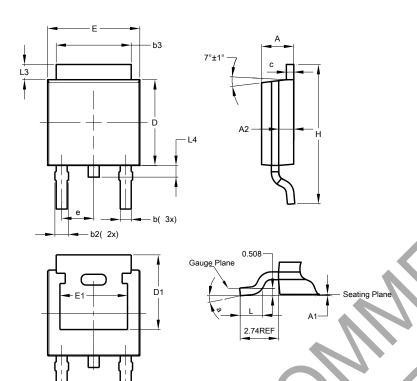


MJD31CQ



Package Outline Dimensions

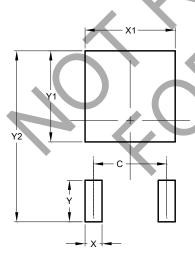
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
C	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21				
e	ı	1	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Í	9.40	10.41	9.91		
_	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
14	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10 700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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